TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT10J321

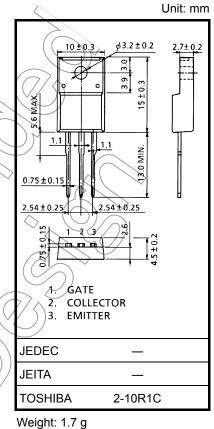
High Power Switching Applications

Fast Switching Applications

- Fourth-generation IGBT
- Enhancement mode type
- Fast switching (FS): Operating frequency up to 50 kHz (reference)
- High speed: $t_f = 0.03 \ \mu s$ (typ.)
- Low switching loss : E_{on} = 0.26 mJ (typ.) : E_{off} = 0.18 mJ (typ.)
- Low saturation voltage: VCE (sat) = 2.0 V (typ.)
- FRD included between emitter and collector

Absolute Maximum Ratings (Ta = 25°C)

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Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	600	∕∕y	
Gate-emitter voltage		V _{GES}	∌ 25	> v	
Continuous Collector current	@ Tc = 100°C	IC -	5	Ā	
	@ Tc = 25°C		10	~	
Pulsed collector current		I _{CP}	(<u>20</u>	A	\backslash
Diode forward current	DC	I _F	10	$\langle \langle \rangle$	\backslash
	Pulsed	IFP	20	R	
Collector power dissipation	@ Tc = 100°C	PG)) 11	w	\leq
	@ Tc = 25°C		29 <		Ť
Junction temperature		$(_{\mathbf{I}_{j}}) $	150)%C	
Storage temperature range		Tstg	-55~150	°C	
					-



Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

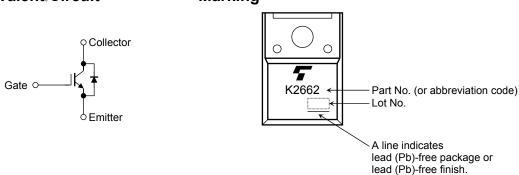
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics		Symbol	Max	Unit
Thermal resistance (IGBT)	\bigcirc	R _{th} (j-c)	4.31	°C/W
Thermal resistance (diode)	$\langle \rangle$	R _{th} (j-c)	4.90	°C/W

Equivalent Circuit

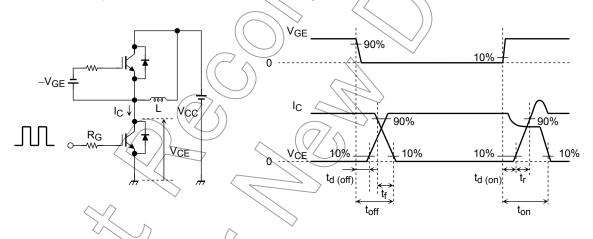




Electrical Characteristics (Ta = 25°C)

Cha	racteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	urrent	I _{GES}	$V_{GE}=\pm 25~V,~V_{CE}=0$			±500	nA
Collector cut-off	current	ICES	$V_{CE} = 600 \text{ V}, \text{ V}_{GE} = 0$			1.0	mA
Gate-emitter cu	t-off voltage	V _{GE (OFF)}	$I_C = 1 \text{ mA}, V_{CE} = 5 \text{ V}$	3.5	_	6.5	V
Collector-emitte	r saturation voltage	V _{CE (sat)}	$I_{C} = 10 \text{ A}, \text{ V}_{GE} = 15 \text{ V}$	$\langle \rangle$	2.0	2.45	V
Input capacitant	ce	Cies	$V_{CE} = 10 \text{ V}, \text{ V}_{GE} = 0, \text{ f} = 1 \text{ MHz}$	Æ) 1550	_	pF
Switching time	Turn-on delay time	t _{d (on)}	. (7	\sum	0.06	_	
	Rise time	tr		\mathcal{Y}	0.03		μs
	Turn-on time	t _{on}	Inductive load $V_{CC} = 300 \text{ V}, \text{ I}_{C} = 10 \text{ A}$		0.17		
	Turn-off delay time	^t d (off)		_	0.24	_	
	Fall time	t _f	$V_{GG} = +15 \text{ V}, \text{ R}_{G} = 68 \Omega$	—	0.03	\rightarrow	
	Turn-off time	t _{off}	(Note 1)		0.30	>	
Switching loss	Turn-on switching loss	E _{on}	(Note 2)	~((0.26) —	mJ
	Turn-off switching loss	E _{off}			0.18		
Peak forward vo	oltage	VF	$I_F = 10 \text{ A}, V_{GE} = 0$	Ð	_	2.0	V
Reverse recove	ry time	t _{rr}	$I_F = 10 \text{ A, } di/dt = -100 \text{ A/}\mu\text{s}$	-	100		ns

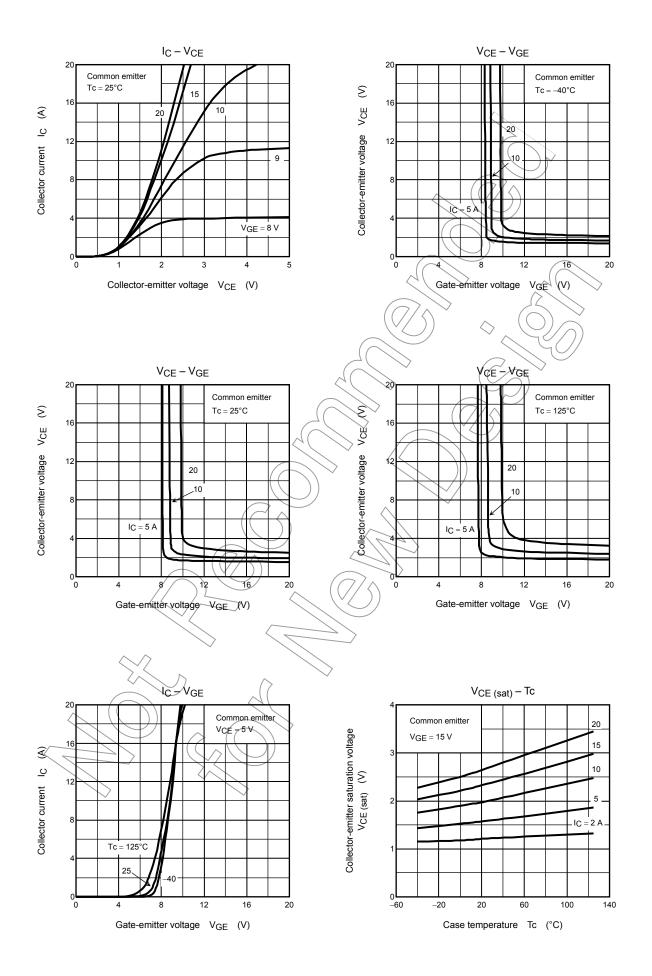
Note 1: Switching time measurement circuit and input/output waveforms

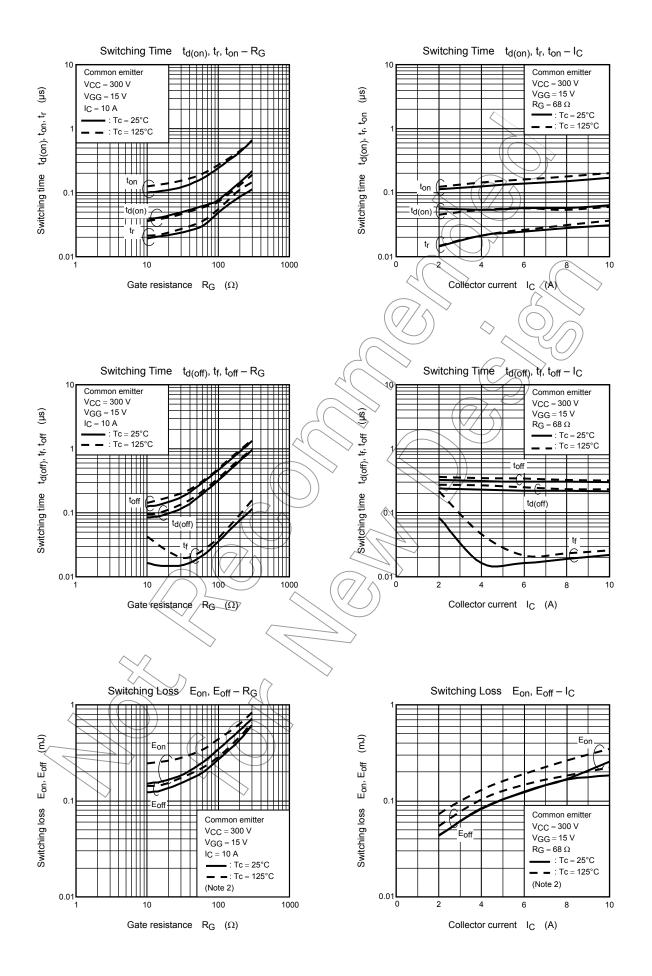


 V_{CE} 90% 10%

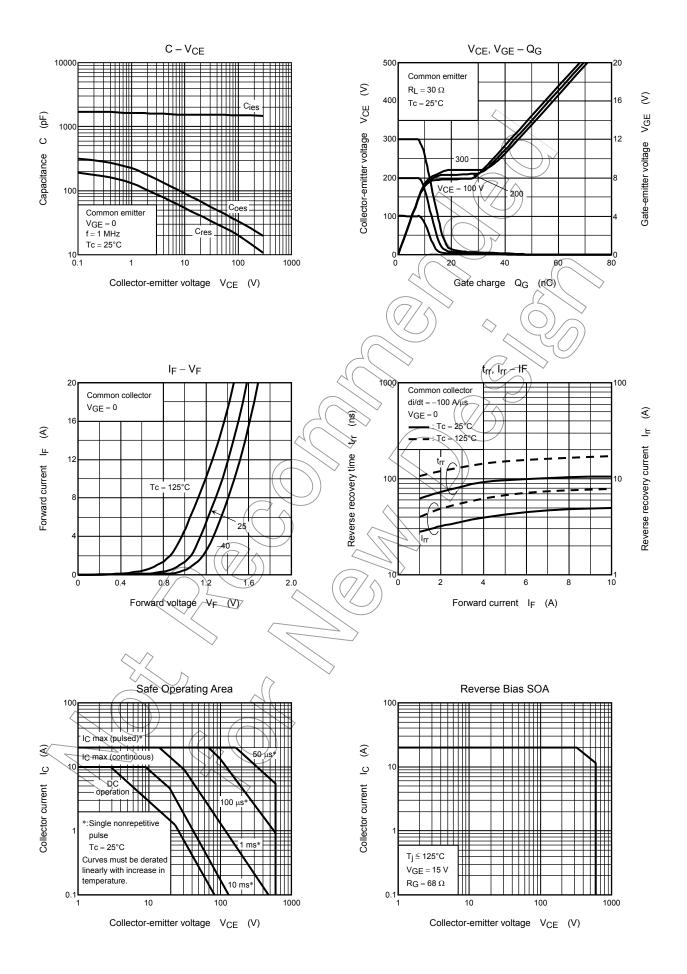
Note 2: Switching loss measurement waveforms

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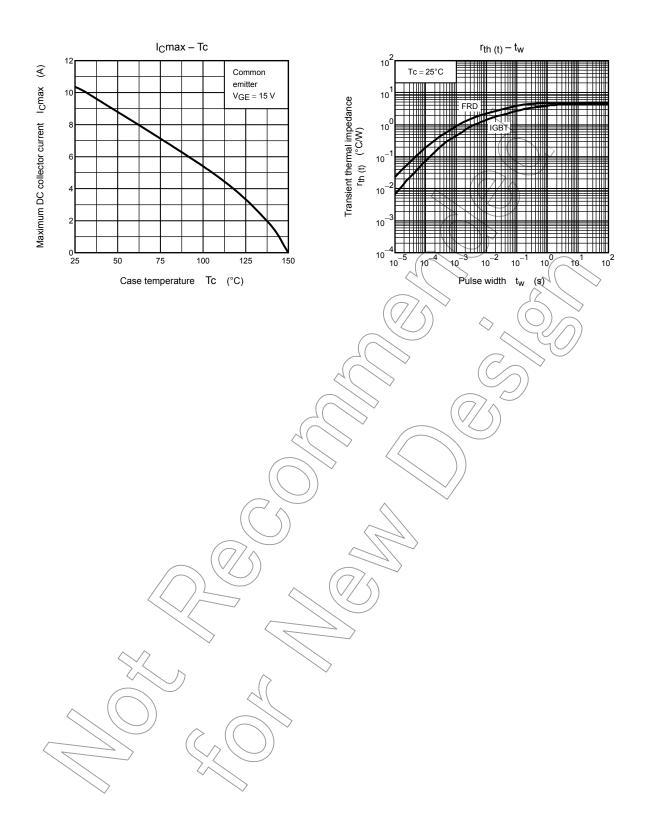




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